




FACULTY OF PHYSICS AND MATHEMATICS

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<p>EDUCATION:</p>	<p>2005- 2009: Urganch State University. (Diplom)</p> <p>2009-2011 : Tashkent State University</p> <p>2011 -2019 teacher Urganch State University.</p> <p>2019- doktorant Urganch State University.</p>
<p>SPECIALITY</p>	<ul style="list-style-type: none"> • Physics.
<p>TEACHING SUBJECTS:</p>	<p>physics of defects in semiconductors, photoelectrical phenomena in semiconductors and in semiconductor devices.</p>
<p>RESEARCH AREAS OF INTEREST:</p>	<p>Modeling of semiconductor nanoscale devices, semiconductor multilayers, semiconductor surfaces, semiconductor – oxide interface, MOS structures, MOSFETs, FinFETS, Junctionless MOSFET, short channel effects, RTN in nanometer MOSFET, subthreshold behavior of MOSFET, CMOS, radiation physics of semiconductor devices.</p>
<p>PRESENT PROJECTS:</p>	<p>2017-2020 “ New approach to investigation of the nature and lateral distribution of the defects at Si-SiO₂ interface and in the oxide layer”. Ministry of innovational development of Uzbekistan.</p> <p>2021-2023. Uzbek-Indian joint project “Self Heating Effect on stacked Nanosheet Field Effect Transistor”</p>
<p>LIST OF SELECTED PAPERS</p>	<ol style="list-style-type: none"> 1. A.E. Atamuratov, R. Granzner , M. Kittler, Z. Atamuratova, M. Halillaev, F. Schwier . Simulation of Random Telegraph Noise in nanometer nMOSFET induced by interface and oxide trapped charge. NATO Advanced Research Workshop on Low Dimensional Functional Materials, October 15-19, 2012, Tashkent 2. A.E. Atamuratov , Z. Atamuratova, M. Halillaev, G. Ghione. Simulation of carrier distribution in nanometer MNOSFET with single charge trapped in oxide and at SiO₂ – Si₃N₄ interface. Materials of International conference Low dimensional nanoscale systems: quantum effects, particle transport and advanced materials. November 6-7,2012, Tashkent. 3. Matyakubov H., Atamuratova Z. A., Abdikarimov A., Halillaev M., Atamuratov A.E.

The method of estimation of single trapped charge position in nanometer MNOSFET oxide layer and Si-SiO₂ interface. Materials of International conference Fundamental and Applied Problems of Physics November 14-16,2013, Tashkent.

4. A.E.Atamuratov, U.A.Aminov, Z.A. Atamuratova, M. Halillaev, A. Abdikarimov , H. Matyakubov. The lateral capacitance of nanometer MNOSFET with a single charge trapped in oxide layer or at SiO₂ - Si₃N₄ interface. Nanosystems: physics, chemistry, mathematics, 2015, 6 (6), p. 837–842

5.A.E. Atamuratov, A. Abdikarimov, M. Khalilloev, Z. A. Atamuratova , R. Rahmanov, A. Garcia-Loureiro, A. Yusupov, Simulation study of dibl effect in 25 nm soi-finfet with the different body shape, Nanosystems: Physics, Chemistry, Mathematics, 2017. 8 (1), p. 71–74

6.A. E. Atamuratov, , M. Khalilloev, , A. Abdikarimov, , Z.A. Atamuratova, M. Kittler, R. Granzner, F. Schwierz, Influence of non-uniform lateral interface defects distribution to the current-voltage characteristic of MOSFET .Nanosystems: physics, chemistry, mathematics, 2017, 8 (1), p. 75–78.

7. Atamuratov A.E.,Abdikarimov A., Atamuratova Z.A., Xolillaev M., Yusupov A. Collection of papers (Urgench state university). Actual problems of modern science, education and training in the region 8-12 page, N1, 2017

8. A.E. Atamuratov, Z.A. Atamuratova, A. Yusupov, A. Ghani,. Characterising lateral capacitance of MNOSFET with localised trapped charge in nitride layer. Results in Physics, V.11, 2018, pp. 656–658..

9.Z. A. Atamuratova, A. Yusupov, B. O. Khalikberdiev, and A. E. Atamuratov Anomalous Behavior of Lateral C–V Characteristic of an MNOS Transistor with an Embedded Local Charge in the Nitride Layer. Technical Physics, 2019, Vol. 64, No. 7, pp. 1006–1009.

10. Atabek E. Atamuratov, Ahmed Yusupov, Zukhra A. Atamuratova, Jean Chamberlain Chedjou and Kyamakya Kyandoghere. Lateral Capacitance–VoltageMethod of NanoMOSFET for Detecting the Hot Carrier Injection. Appl. Sci. 2020, 10(21), 7935; doi:10.3390/app10217935